

## **KSD560**

### **Low Frequency Power Amplifier**

- Low Speed Switching Industrial Use
- Complement to KSB601



1.Base 2.Collector 3.Emitter

## **NPN Epitaxial Silicon Darlington Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	150	٧
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	5	Α
I <sub>CP</sub>	*Collector Current (Pulse)	8	Α
I <sub>B</sub>	Base Current	0.5	Α
P <sub>C</sub>	Collector Dissipation (T <sub>a</sub> =25°C)	1.5	W
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	30	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

<sup>\*</sup> PW≤10ms, Duty Cycle≤50%

## Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 100V, I_{E} = 0$			1	μΑ
h <sub>FE1</sub>	*DC Current Gain	$V_{CE} = 2V, I_{C} = 3A$	2K	6K	15K	
h <sub>FE2</sub>		$V_{CE} = 2V, I_{C} = 5A$	500			
V <sub>CE</sub> (sat)	*Collector-Emitter Saturation Voltage	$I_C = 3A$ , $I_B = 3mA$		0.9	1.5	V
V <sub>BE</sub> (sat)	*Base-Emitter SaturationVoltage	$I_C = 3A$ , $I_B = 3mA$		1.6	2	V
t <sub>ON</sub>	Turn ON Time	$V_{CC} = 50V, I_{C} = 3A$		1		μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = 3mA$		3.5	·	μs
f <sub>T</sub>	Fall Time	$R_L = 16.7\Omega$		1.2	·	μs

<sup>\*</sup> Pulse Test: PW≤350µs, Duty Cycle≤2% Pulsed

## **h**<sub>FE</sub> Classification

Classification	R	0	Y	
h <sub>FE1</sub>	2000 ~ 5000	3000 ~ 7000	5000 ~ 15000	

# **Typical Characteristics**

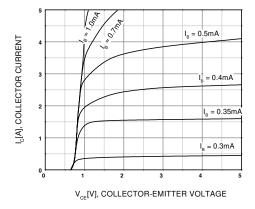


Figure 1. Static Characteristic

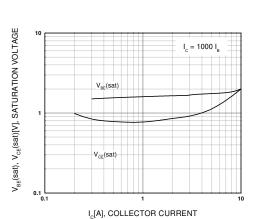


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

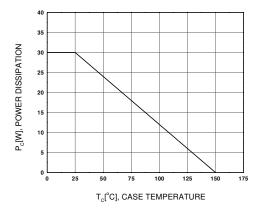


Figure 5. Power Derating

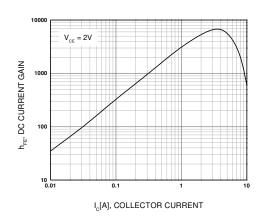


Figure 2. DC current Gain

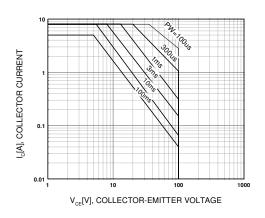
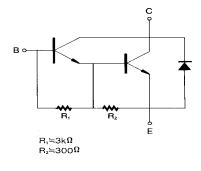


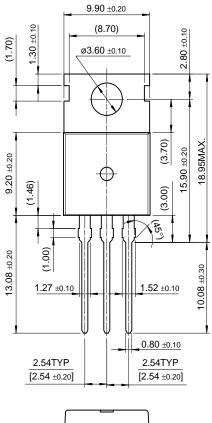
Figure 4. Safe Operating Area

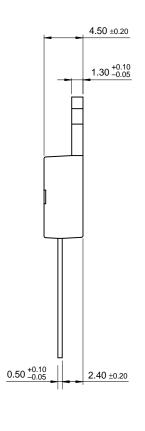


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## **Package Demensions**

## TO-220





10.00 ±0.20

**Dimensions in Millimeters** 

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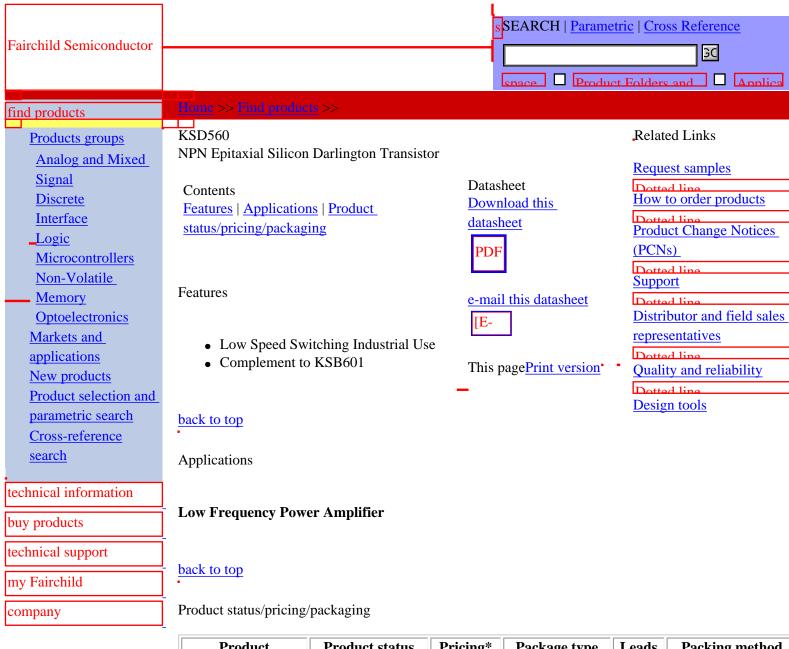
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### **Definition of Terms**

Datasheet Identification	Product Status	Definition		
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.		
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Product	Product status	Pricing*	Package type	Leads	Packing method
KSD560R	Full Production	\$0.357	TO-220	3	BULK
KSD560RTSTU	Full Production	\$0.357	TO-220	3	RAIL
KSD560Y	Full Production	\$0.357	TO-220	3	BULK
KSD560RTU	Full Production	\$0.357	TO-220	3	RAIL
KSD560YTU	Full Production	\$0.357	TO-220	3	RAIL
KSD560OTU	Full Production	\$0.357	TO-220	3	RAIL

<sup>\* 1,000</sup> piece Budgetary Pricing

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